

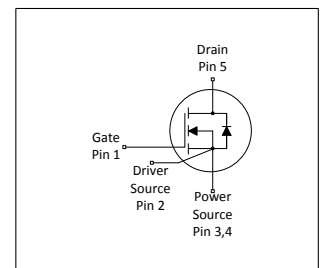
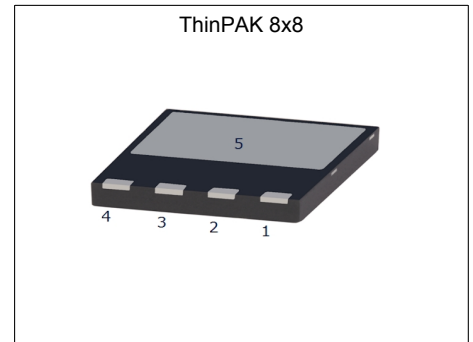
MOSFET

600V CoolMOS™ CP Power Transistor

The CoolMOS™ CP series offers devices which provide all benefits of a fast switching SJ MOSFET while not sacrificing ease of use. Extremely low switching and conduction losses make switching applications even more efficient, more compact, lighter, and cooler..

ThinPAK

ThinPAK is a new leadless SMD package for HV MOSFETs. The new package has a very small footprint of only 64mm² (vs. 150mm² for the D²PAK) and a very low profile with only 1mm height (vs. 4.4mm for the D²PAK). The significantly smaller package size, combined with benchmark low parasitic inductances, provides designers with a new and effective way to decrease system solution size in power-density driven designs.



Features

- Reduced board space consumption
- Increased power density
- Short commutation loop
- Smooth switching waveform
- easy to use products
- Extremely low losses due to very low FOM $R_{DS(on)} \cdot Q_g$ and E_{oss}
- Qualified according to JEDEC (J-STD20 and JESD22) for target applications (Server, Adapter)
- Pb-free plating, Halogen free

Potential applications

Server, Adapter

Table 1 Key Performance Parameters

Parameter	Value	Unit
$V_{ds} @ T_{jmax}$	650	V
$R_{DS(on),max}$	0.199	Ω
$Q_{g,typ}$	32	nC
$I_{D,pulse}$	63	A
$E_{oss} @ 400V$	6.1	μJ
Body diode di_f/dt	200	A/ μs

Type / Ordering Code	Package	Marking	Related Links
IPL60R199CP	PG-VSON-4	6R199P	see Appendix A

Table of Contents

Description	1
Maximum ratings	3
Thermal characteristics	3
Electrical characteristics	4
Electrical characteristics diagrams	6
Test Circuits	10
Package Outlines	11
Appendix A	12
Revision History	13
Trademarks	13
Disclaimer	13

1 Maximum ratings
at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	16.4 10.0	A	$T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	63	A	$T_C=25^\circ\text{C}$
Avalanche energy, single pulse	E_{AS}	-	-	436	mJ	$I_D=6.6\text{ A}; V_{DD} = 50\text{ V}$
Avalanche energy, repetitive ³⁾	E_{AR}	-	-	0.66	mJ	$I_D=6.6\text{ A}; V_{DD} = 50\text{ V}$
Avalanche current, repetitive ³⁾	I_{AR}	-	-	6.6	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	50	V/ns	$V_{DS} = 0\dots480\text{ V}$
Gate source voltage	V_{GS}	-20 -30	-	20 30	V	static; AC ($f > 1\text{ Hz}$)
Power dissipation	P_{tot}	-	-	139	W	$T_C=25^\circ\text{C}$
Operating Temperature	T_j	-40	-	150	$^\circ\text{C}$	-
Storage Temperature	T_{stg}	-40	-	125	$^\circ\text{C}$	-
Continuous diode forward current	I_S	-	-	16.4	A	$T_C=25^\circ\text{C}$
Diode pulse current ²⁾	$I_{S,pulse}$	-	-	63	A	$T_C = 25^\circ\text{C}$
Reverse diode dv/dt ⁴⁾	dv/dt	-	-	15	V/ns	$V_{DS} = 0\dots400\text{ V}, I_{SD} \leq I_D, T_j=25^\circ\text{C}$ see table 8
Maximum diode commutation speed	di_f/dt	-	-	200	A/ μs	$V_{DS} = 0\dots400\text{ V}, I_{SD} \leq I_D, T_j=25^\circ\text{C}$ see table 8

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	0.9	$^\circ\text{C/W}$	-
Thermal resistance, junction - ambient ⁵⁾	R_{thJA}	-	-	45	$^\circ\text{C/W}$	SMD version, device on PCB, 6cm ² cooling area
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	-	-	260	$^\circ\text{C}$	reflow MSL2a

1) Limited by $T_{j,max}$. Maximum duty cycle

2) Pulse width t_p limited by $T_{j,max}$

3) Repetitive avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR} \cdot f$; Pulse width t_p limited by $T_{j,max}$

4) Identical low side and high side switch with identical R_G

5) Device on 40mm*40mm*1.5mm one layer epoxy PCB FR4 with 6cm² copper area (thickness 70 μm) for drain connection. PCB is vertical without air stream cooling.

3 Electrical characteristics

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	600	-	-	V	$V_{GS}=0\text{ V}$, $I_D=0.25\text{ mA}$
Gate threshold voltage	$V_{(GS)th}$	2.5	3	3.5	V	$V_{DS}=V_{GS}$, $I_D=0.66\text{ mA}$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=600\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ }^\circ\text{C}$ $V_{DS}=600\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=150\text{ }^\circ\text{C}$
Gate-source leakage current	I_{GSS}	-	-	100	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.18	0.199	Ω	$V_{GS}=10\text{ V}$, $I_D=9.9\text{ A}$, $T_j=25\text{ }^\circ\text{C}$ $V_{GS}=10\text{ V}$, $I_D=9.9\text{ A}$, $T_j=150\text{ }^\circ\text{C}$
Gate resistance	R_G	-	2	-	Ω	$f=1\text{ MHz}$, open drain

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	1520	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=100\text{ V}$, $f=1\text{ MHz}$
Output capacitance	C_{oss}	-	72	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=100\text{ V}$, $f=1\text{ MHz}$
Effective output capacitance, energy related ¹⁾	$C_{o(er)}$	-	69	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=0\dots480\text{ V}$
Effective output capacitance, time related ²⁾	$C_{o(tr)}$	-	180	-	pF	$I_D=\text{constant}$, $V_{GS}=0\text{ V}$, $V_{DS}=0\dots480\text{ V}$
Turn-on delay time	$t_{d(on)}$	-	10	-	ns	$V_{DD}=400\text{ V}$, $V_{GS}=13\text{ V}$, $I_D=9.9\text{ A}$, $R_G=3.3\Omega$; see table 9
Rise time	t_r	-	5	-	ns	$V_{DD}=400\text{ V}$, $V_{GS}=13\text{ V}$, $I_D=9.9\text{ A}$, $R_G=3.3\Omega$; see table 9
Turn-off delay time	$t_{d(off)}$	-	50	-	ns	$V_{DD}=400\text{ V}$, $V_{GS}=13\text{ V}$, $I_D=9.9\text{ A}$, $R_G=3.3\Omega$; see table 9
Fall time	t_f	-	5	-	ns	$V_{DD}=400\text{ V}$, $V_{GS}=13\text{ V}$, $I_D=9.9\text{ A}$, $R_G=3.3\Omega$; see table 9

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	8	-	nC	$V_{DD}=480\text{ V}$, $I_D=9.9\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge	Q_{gd}	-	11	-	nC	$V_{DD}=480\text{ V}$, $I_D=9.9\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total	Q_g	-	32	-	nC	$V_{DD}=480\text{ V}$, $I_D=9.9\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	5.0	-	V	$V_{DD}=480\text{ V}$, $I_D=9.9\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$

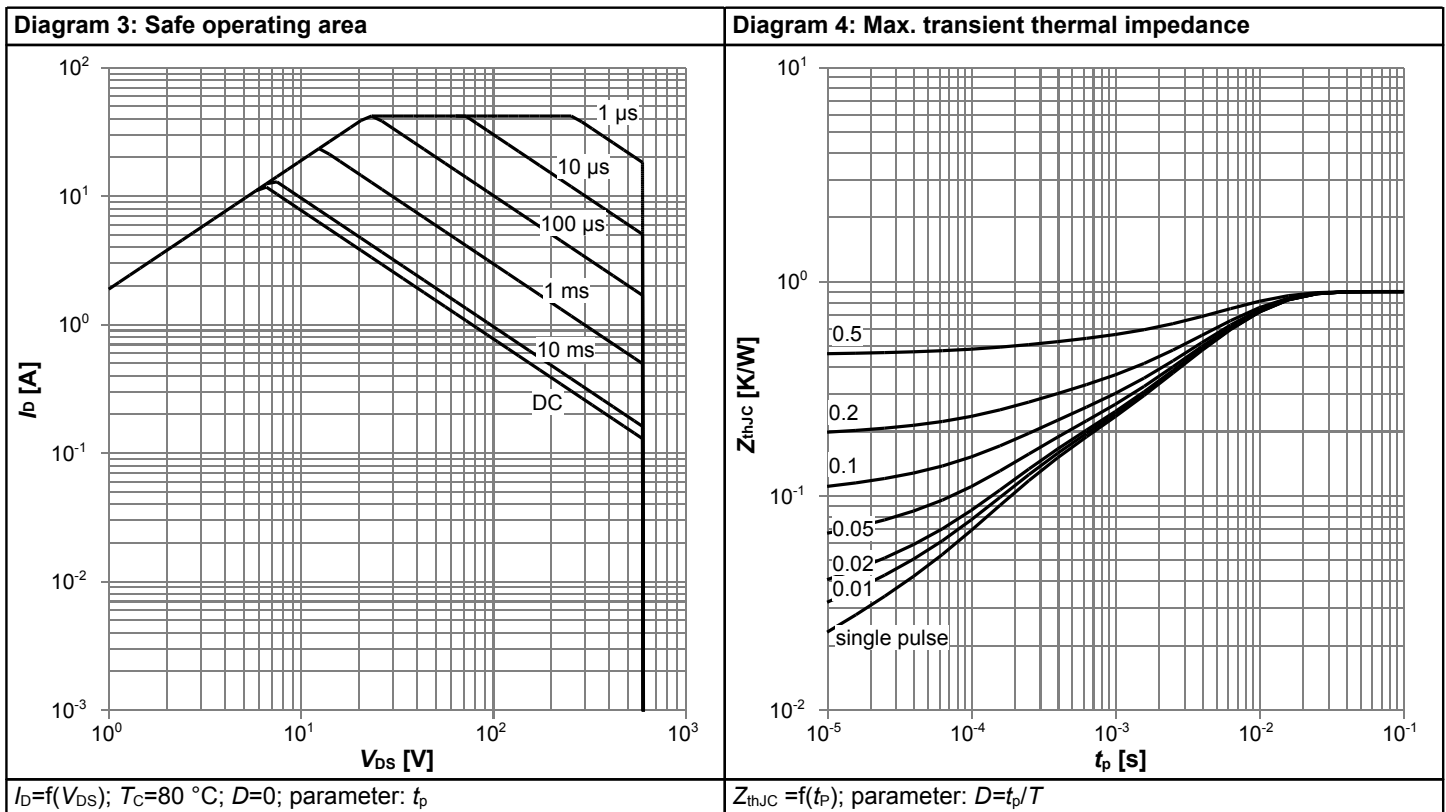
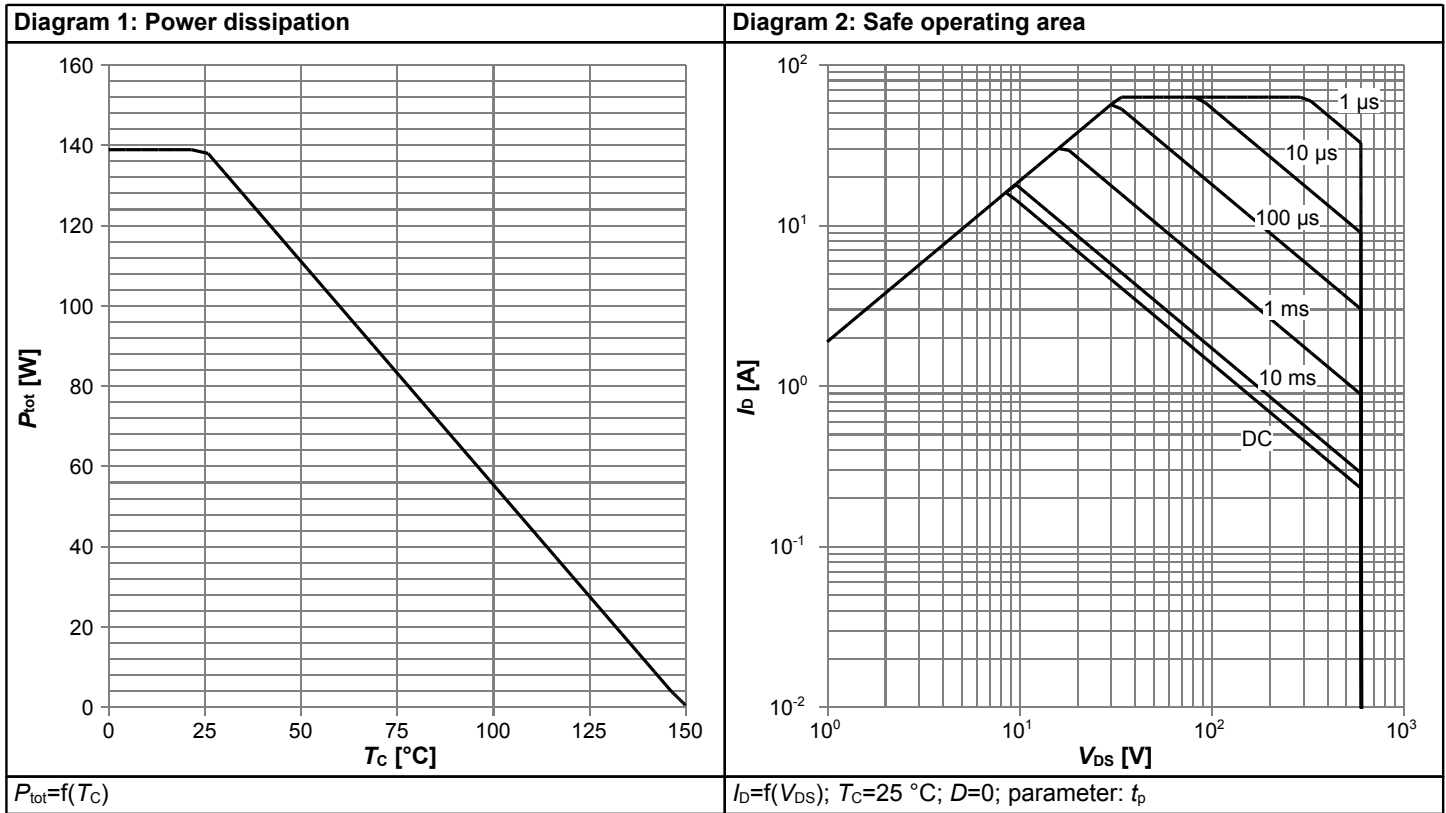
¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$

²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$

Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.9	-	V	$V_{GS}=0\text{ V}$, $I_F=9.9\text{ A}$, $T_j=25\text{ °C}$
Reverse recovery time	t_{rr}	-	340	-	ns	$V_R=400\text{ V}$, $I_F=9.9\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$ see table 8
Reverse recovery charge	Q_{rr}	-	5.5	-	μC	$V_R=400\text{ V}$, $I_F=9.9\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$ see table 8
Peak reverse recovery current	I_{rrm}	-	33	-	A	$V_R=400\text{ V}$, $I_F=9.9\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$ see table 8

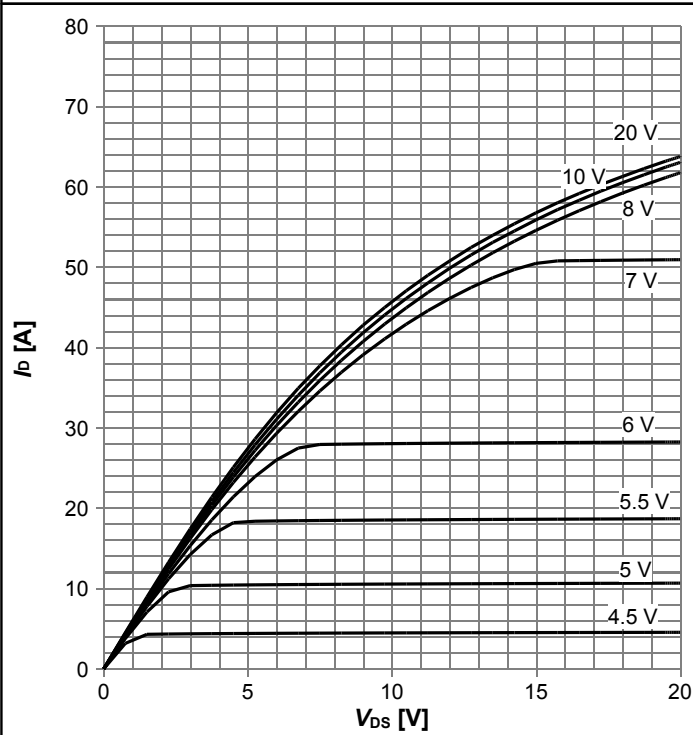
4 Electrical characteristics diagrams



600V CoolMOS™ CP Power Transistor

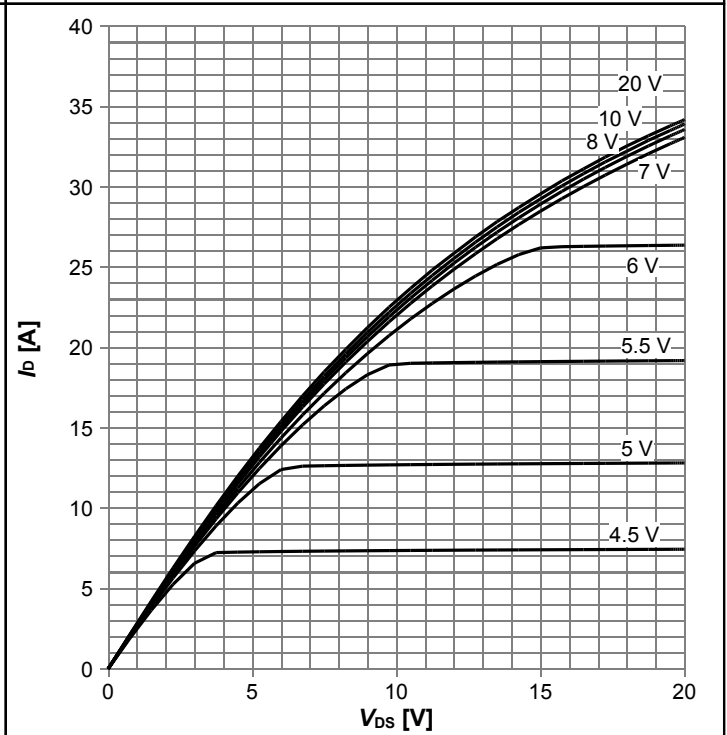
IPL60R199CP

Diagram 5: Typ. output characteristics



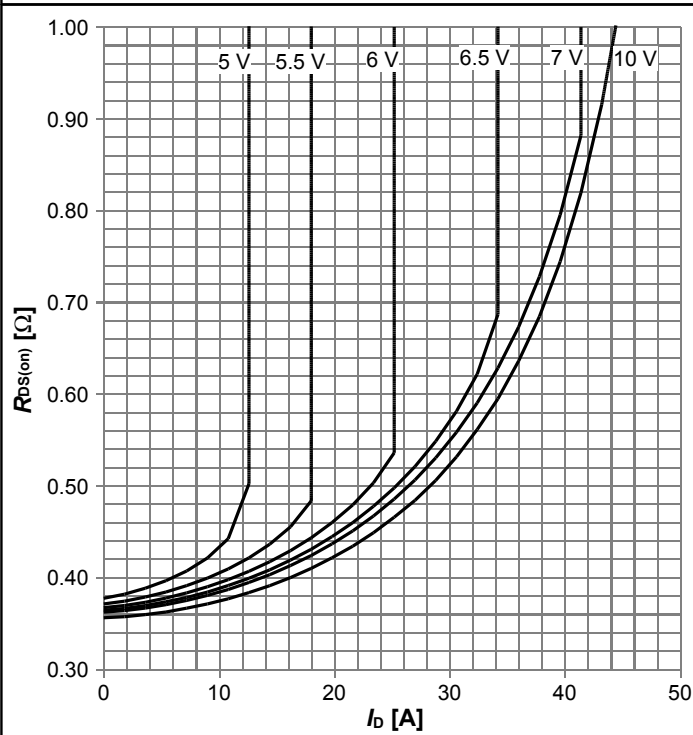
$I_D=f(V_{DS})$; $T_j=25\text{ }^\circ\text{C}$; parameter: V_{GS}

Diagram 6: Typ. output characteristics



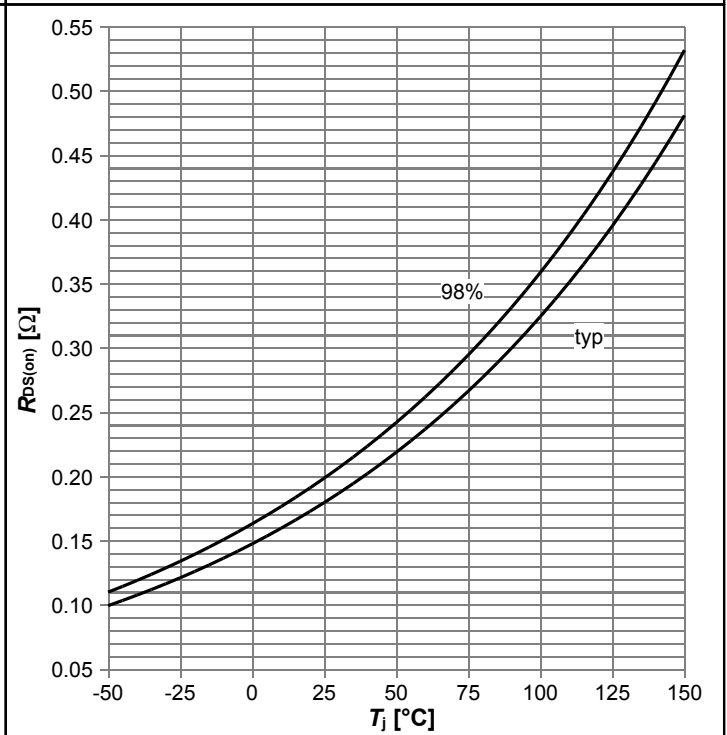
$I_D=f(V_{DS})$; $T_j=125\text{ }^\circ\text{C}$; parameter: V_{GS}

Diagram 7: Typ. drain-source on-state resistance



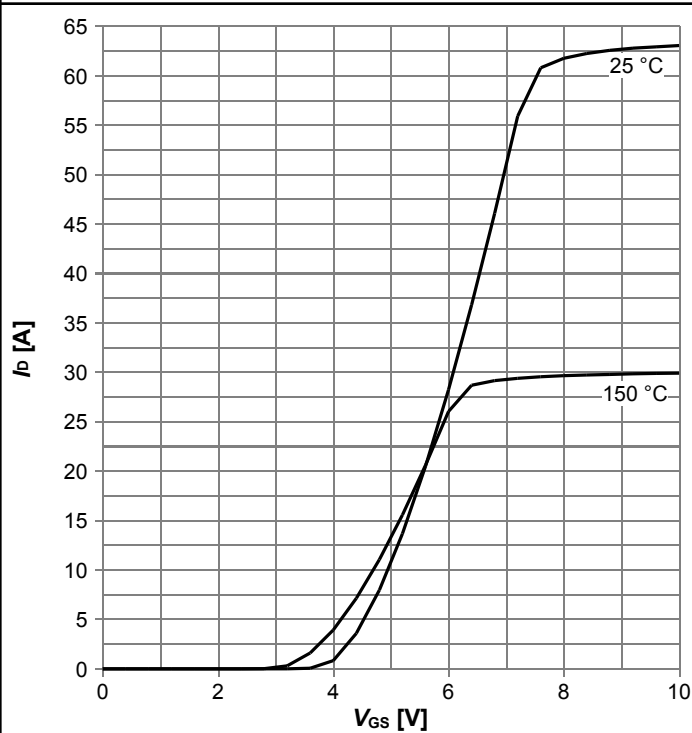
$R_{DS(on)}=f(I_D)$; $T_j=125\text{ }^\circ\text{C}$; parameter: V_{GS}

Diagram 8: Drain-source on-state resistance



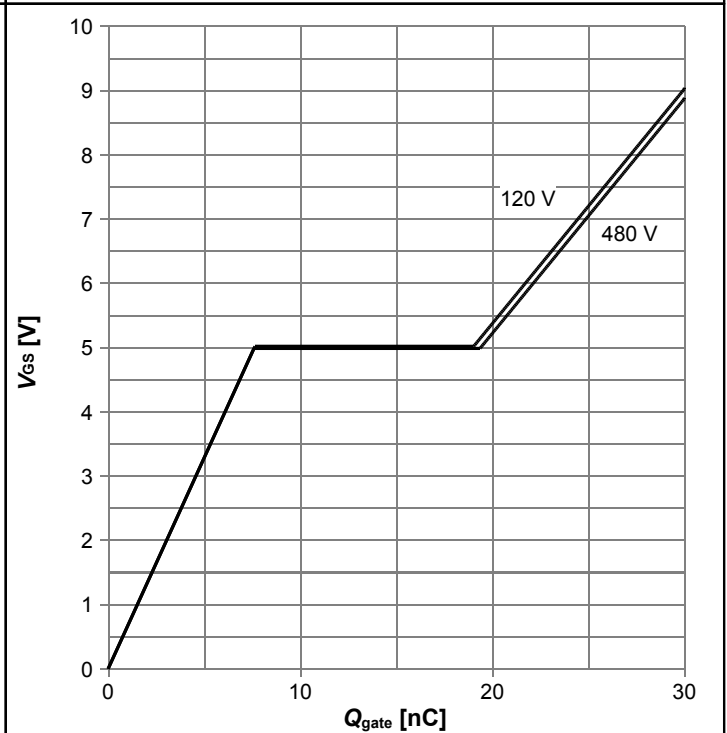
$R_{DS(on)}=f(T_j)$; $I_D=9.9\text{ A}$; $V_{GS}=10\text{ V}$

Diagram 9: Typ. transfer characteristics



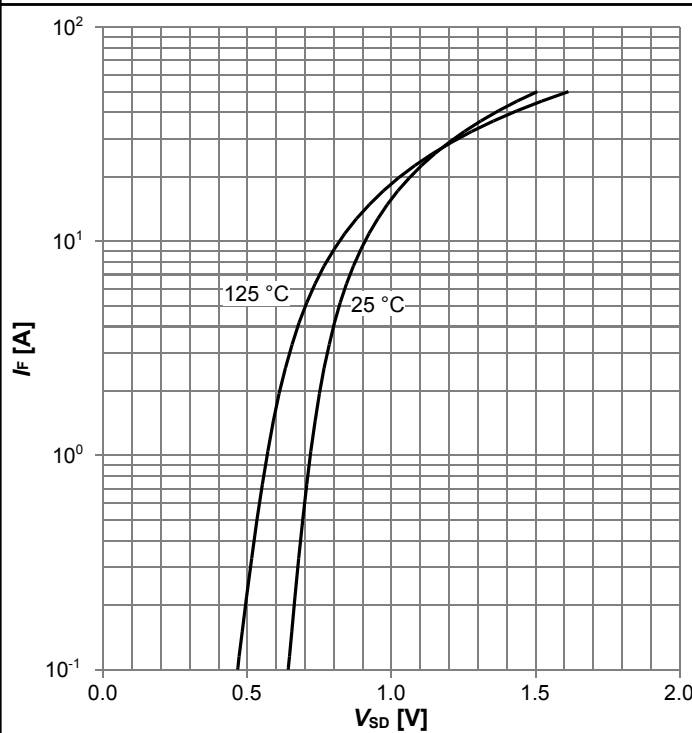
$I_D = f(V_{GS}); V_{DS} = 20V; \text{parameter: } T_j$

Diagram 10: Typ. gate charge



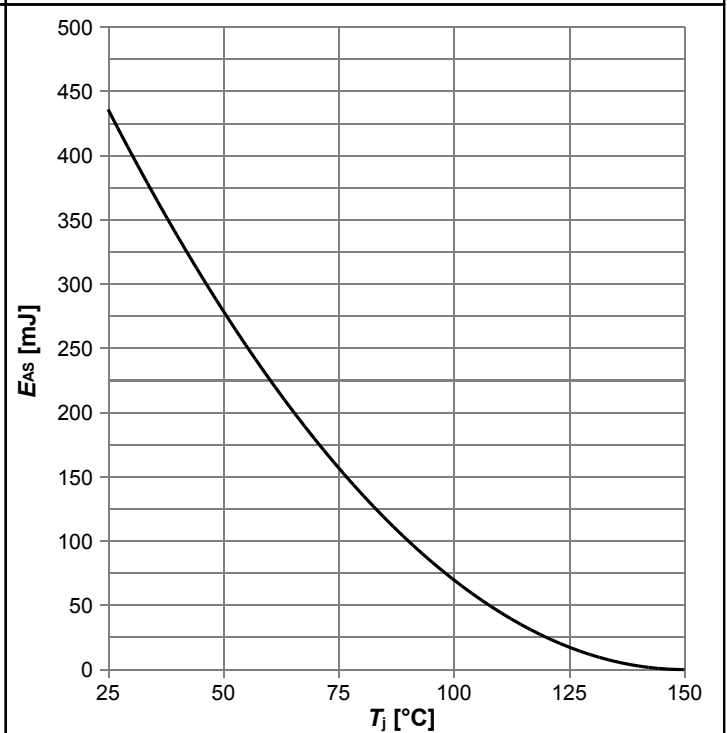
$V_{GS} = f(Q_{gate}); I_D = 9.9 \text{ A pulsed}; \text{parameter: } V_{DD}$

Diagram 11: Forward characteristics of reverse diode



$I_F = f(V_{SD}); \text{parameter: } T_j$

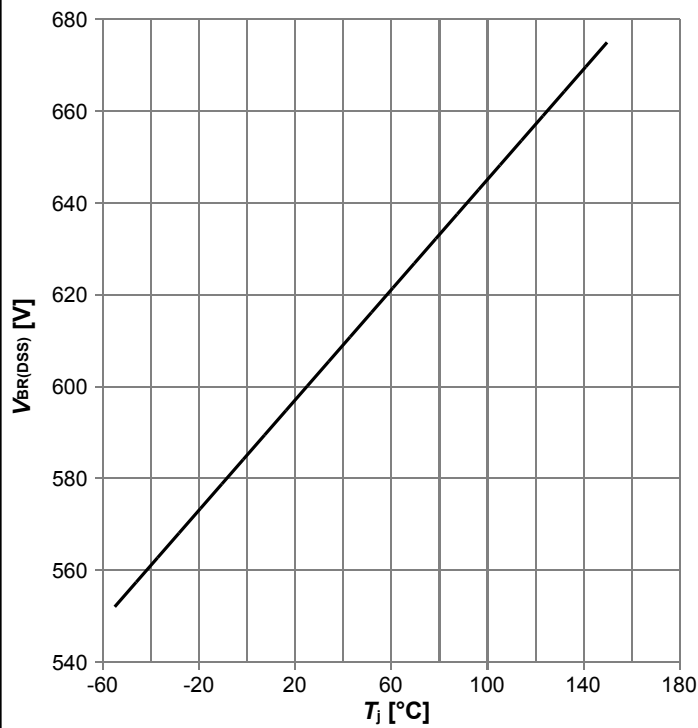
Diagram 12: Avalanche energy



$E_{AS} = f(T_j); I_D = 6.6 \text{ A}; V_{DD} = 50 \text{ V}$

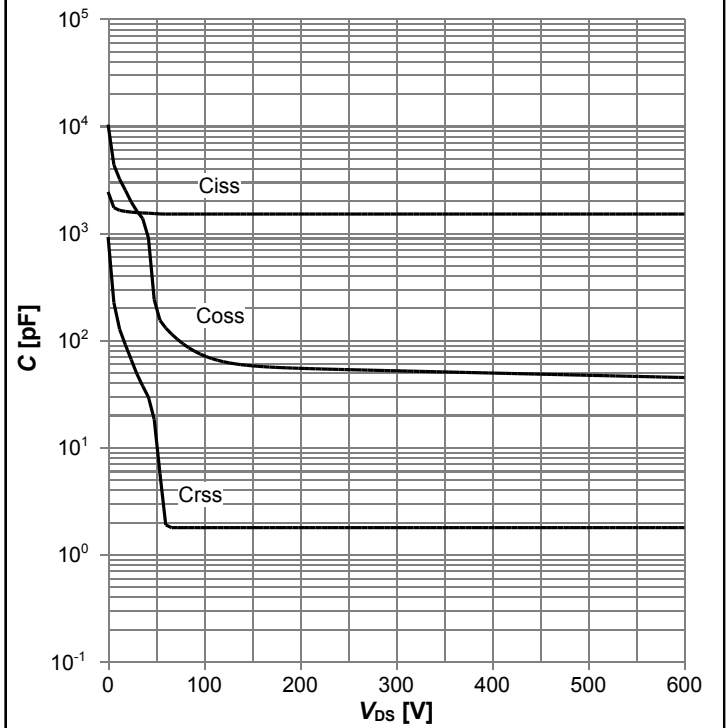
600V CoolMOS™ CP Power Transistor
IPL60R199CP

Diagram 13: Drain-source breakdown voltage



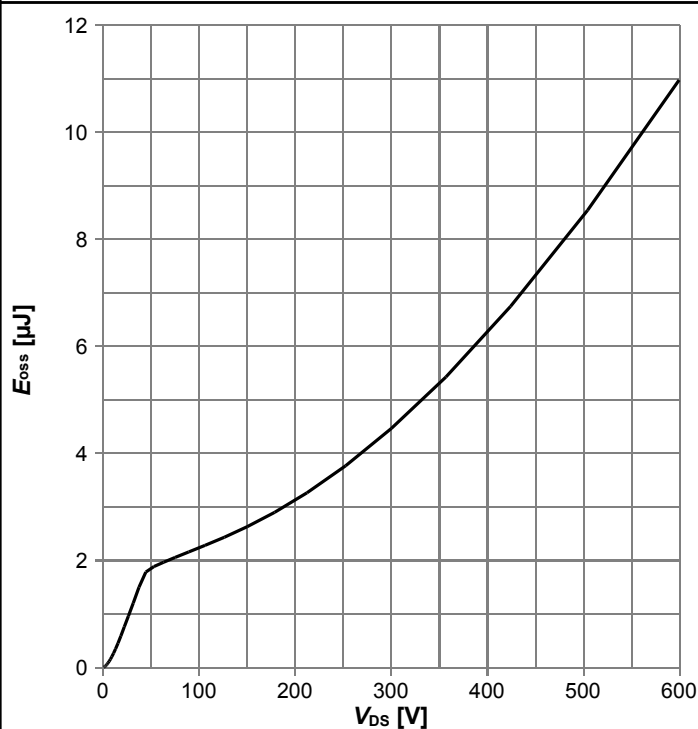
$V_{BR(DSS)}=f(T_j); I_D=0.25 \text{ mA}$

Diagram 14: Typ. capacitances



$C=f(V_{DS}); V_{GS}=0 \text{ V}; f=1 \text{ MHz}$

Diagram 15: Typ. Coss stored energy



$E_{oss}=f(V_{DS})$

5 Test Circuits

Table 8 Diode characteristics

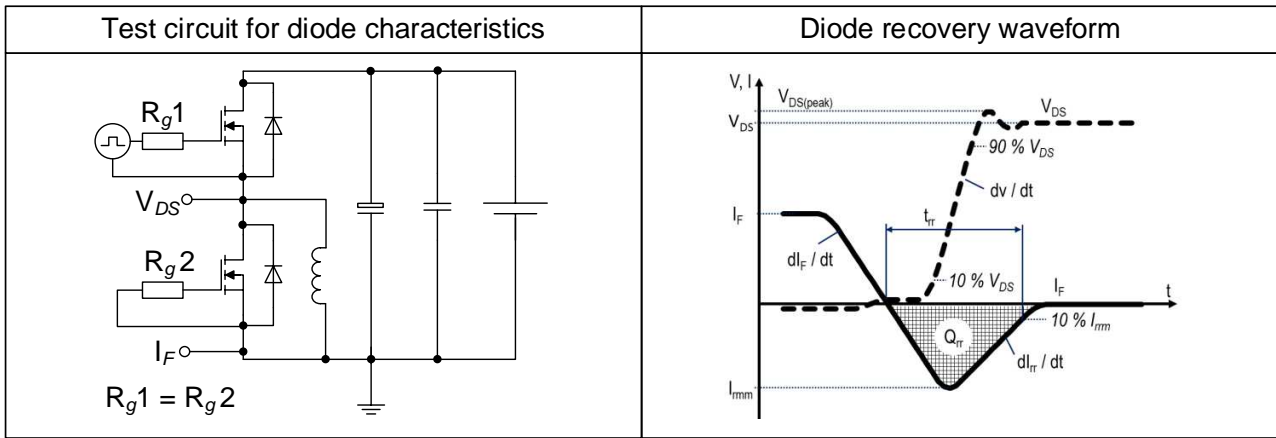


Table 9 switching times (ss)

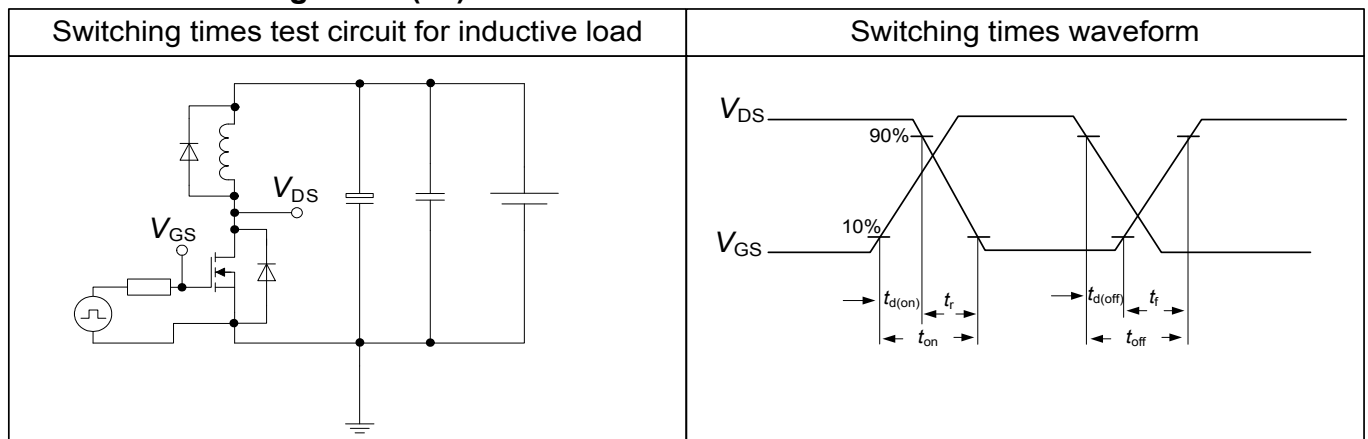
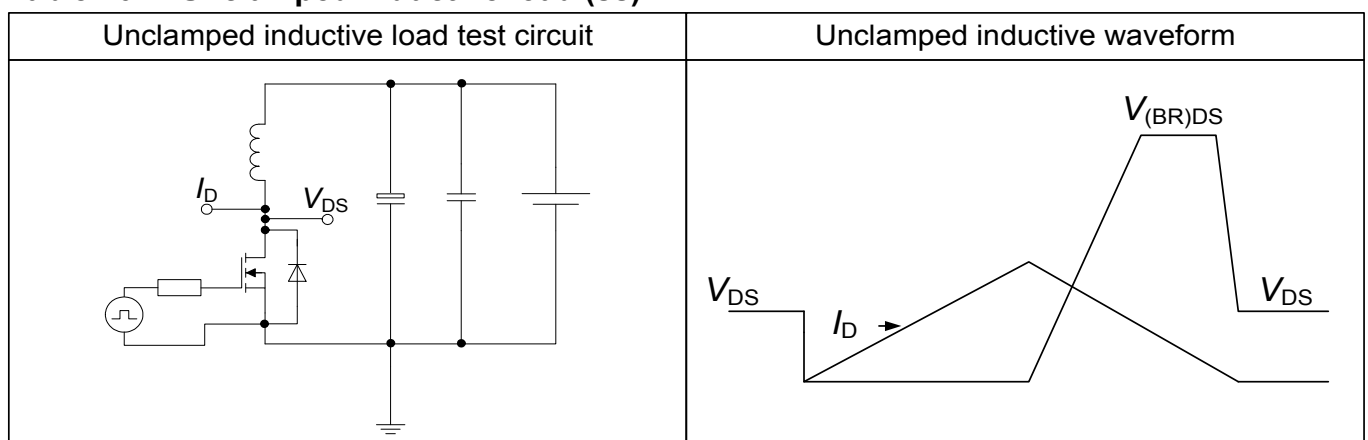


Table 10 Unclamped inductive load (ss)



6 Package Outlines

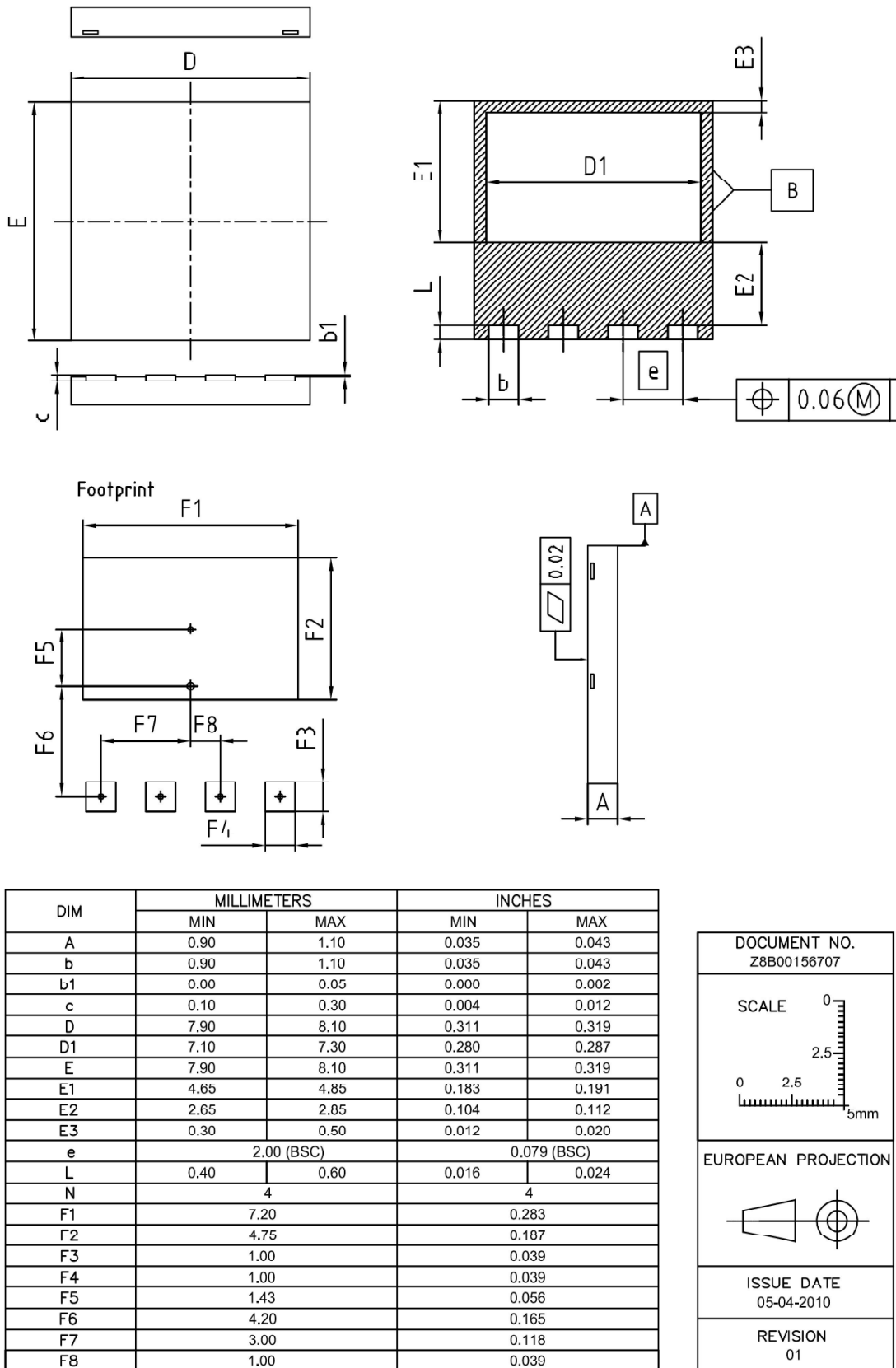


Figure 1 Outline PG-VSON-4, dimensions in mm/inches

7 Appendix A

Table 11 Related Links

- **IFX CoolMOS Webpage:** www.infineon.com
- **IFX Design tools:** www.infineon.com

Revision History

IPL60R199CP

Revision: 2017-09-06, Rev. 2.4

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.3	2015-10-23	Update of ID pulse according to SOA Diagram on page 2 and 3
2.4	2017-09-06	Updated MSL; style updated

Trademarks of Infineon Technologies AG

AURIX™, C166™, CanPAK™, CIPOS™, CoolGaN™, CoolMOS™, CoolSET™, CoolSiC™, CORECONTROL™, CROSSAVE™, DAVE™, DI-POL™, DrBlade™, EasyPIM™, EconoBRIDGE™, EconoDUAL™, EconoPACK™, EconoPIM™, EiceDRIVER™, eupec™, FCOS™, HITFET™, HybridPACK™, Infineon™, ISOFACE™, IsoPACK™, i-Wafer™, MIPAQ™, ModSTACK™, my-d™, NovalithIC™, OmniTune™, OPTIGA™, OptiMOS™, ORIGA™, POWERCODE™, PRIMARION™, PrimePACK™, PrimeSTACK™, PROFET™, PRO-SIL™, RASIC™, REAL3™, ReverSave™, SatRIC™, SIEGET™, SiPMOS™, SmartLEWIS™, SOLID FLASH™, SPOC™, TEMPFET™, thinQ!™, TRENCHSTOP™, TriCore™.

Trademarks updated August 2015

Other Trademarks

All referenced product or service names and trademarks are the property of their respective owners.

We Listen to Your Comments

Any information within this document that you feel is wrong, unclear or missing at all? Your feedback will help us to continuously improve the quality of this document. Please send your proposal (including a reference to this document) to:

erratum@infineon.com

Published by
Infineon Technologies AG
81726 München, Germany
© 2017 Infineon Technologies AG
All Rights Reserved.

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffenhheitsgarantie").

With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

In addition, any information given in this document is subject to customer's compliance with its obligations stated in this document and any applicable legal requirements, norms and standards concerning customer's products and any use of the product of Infineon Technologies in customer's applications.

The data contained in this document is exclusively intended for technically trained staff. It is the responsibility of customer's technical departments to evaluate the suitability of the product for the intended application and the completeness of the product information given in this document with respect to such application.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

The Infineon Technologies component described in this Data Sheet may be used in life-support devices or systems and/or automotive, aviation and aerospace applications or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support, automotive, aviation and aerospace device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MOSFET](#) category:

Click to view products by [Infineon](#) manufacturer:

Other Similar products are found below :

[614233C](#) [648584F](#) [IRFD120](#) [JANTX2N5237](#) [FCA20N60_F109](#) [FDZ595PZ](#) [2SK2545\(Q,T\)](#) [405094E](#) [423220D](#) [TPCC8103,L1Q\(CM](#)
[MIC4420CM-TR](#) [VN1206L](#) [614234A](#) [715780A](#) [NTNS3166NZT5G](#) [SSM6J414TU,LF\(T](#) [751625C](#) [BUK954R8-60E](#) [GROUP A 5962-](#)
[8877003PA](#) [NTE6400](#) [SQJ402EP-T1-GE3](#) [2SK2614\(TE16L1,Q\)](#) [2N7002KW-FAI](#) [DMN1017UCP3-7](#) [EFC2J004NUZTDG](#) [ECH8691-TL-W](#)
[FCAB21350L1](#) [P85W28HP2F-7071](#) [DMN1053UCP4-7](#) [NTE221](#) [NTE222](#) [NTE2384](#) [NTE2903](#) [NTE2941](#) [NTE2945](#) [NTE2946](#) [NTE2960](#)
[NTE2967](#) [NTE2969](#) [NTE2976](#) [NTE6400A](#) [NTE2910](#) [NTE2916](#) [NTE2956](#) [NTE2911](#) [DMN2080UCB4-7](#) [TK10A80W,S4X\(S](#)
[SSM6P69NU,LF](#) [DMP22D4UFO-7B](#) [DMN1006UCA6-7](#)